Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	10	(("6127691") or ("6285695") or ("6396863") or ("6400743") or ("6516016") or ("6546033") or ("6580738") or ("5960020") or ("4371966") or ("4282494")).PN.	USPAT	OR	OFF	2004/12/17 11:20
L2	3932	372/45.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/17 11:20
L3	1112	372/45.ccls. and (substrate and active and cladding and contact near3 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/17 11:21
L4	1112	372/45.ccls. and (substrate and active and cladding and (contact near3 layer))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/17 11:21
L5	526	372/45.ccls. and (substrate and active and cladding and (contact near3 layer) and ridge)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/17 11:21
L6	186	372/45.ccls. and (substrate and active and cladding and (contact near3 layer) and ridge and resonator)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/17 11:21
L7	123	372/45.ccls. and (substrate and active and cladding and (contact near3 layer) and ridge and resonator and insulat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/17 11:21
L8	130	372/45.ccls. and (substrate and active and cladding and (contact near3 layer) and ridge and resonat$4 and insulat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/17 11:22
L9	92	372/45.ccls. and (substrate and active and cladding and (contact near3 layer) and ridge and resonat$4 and insulat$4 and (current near3 (blocking or injection)))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/17 11:22
L10	84	372/45.ccls. and (substrate and active and cladding and (contact near3 layer) and ridge and resonat$4 and insulat$4 and (current near3 (blocking or injection)) and (double or two))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/17 11:29
L11	7	("6127691" | "6285695" | "6356572" | "6396863" | "6400743" | "6516016" | "6546033").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/17 11:26

L12	7	(("6127691") or ("6285695") or ("6356572") or ("6396863") or ("6400743") or ("6516016") or ("6546033")).PN.	USPAT	OR	OFF	2004/12/17 11:28
L13	81	372/46.ccls. and (substrate and active and cladding and (contact near3 layer) and ridge and resonat$4 and insulat$4 and (current near3 (blocking or injection)) and (double or two))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/17 11:29
L14	205	semiconductor and (substrate and active and cladding and (contact near3 layer) and ridge and resonat$4 and insulat$4 and (current near3 (blocking or injection)) and (double or two))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/17 11:30
S1	33	(US-6516016-$ or US-6396863-$ or US-6400743-$ or US-6356572-$ or US-6127691-$ or US-6018539-$ or US-5960020-$ or US-5953358-$ or US-5488678-$ or US-6285695-$ or US-4270096-$ or US-4371966-$ or US-4282494-$ or US-4758535-$ or US-5161166-$ or US-5089437-$ or US-4794610-$ or US-4791635-$ or US-5394421-$ or US-6744797-$ or US-6654397-$ or US-6618420-$ or US-6580738-$ or US-6546033-$ or US-6541291-$).did. or (US-20020146051-$ or US-20020061044-$ or US-20020024985-$ or US-20020015428-$ or US-20010021213-$).did. or (JP-63038279-$ or JP-05327112-$).did. or (US-20020146051-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2004/07/26 10:49
S2	20	crystal and "l46"	USPAT	OR	OFF	2004/07/26 10:49
S3	4141	semiconductor and substrate and active and cladding and contact near3 layer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/17 11:18
S4	2992	372/46.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:20
S5	3772	372/45.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:56

S6	948	372/44.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:20
S7	662	372/49.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:21
S8	1955	372/50.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:21
S9	5577	372/43.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:21
S10	1277	372/75.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:21
S11	1278	372/96.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:22
S12	530	372/97.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:22
S13	1837	semiconductor and substrate and active and cladding and (contact near3 layer) and (insulate or insulating)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:23
S14	1475	semiconductor and substrate and active and cladding and (contact near3 layer) and (insulate or insulating) and (electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:23
S15	618	semiconductor and substrate and active and cladding and (contact near3 layer) and (insulate or insulating) and (electrode) and (ridge)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:24
S16	215	semiconductor and substrate and active and cladding and (contact near3 layer) and (insulate or insulating) and (electrode) and (ridge) and (current near3 injection)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:24

S17	115	semiconductor and substrate and active and cladding and (contact near3 layer) and (insulate or insulating) and (electrode) and (ridge) and (current near3 injection) and (resonator or resonant)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:25
S18	32	semiconductor and substrate and active and cladding and (contact near3 layer) and (insulate or insulating) and (electrode) and (ridge) and (current near3 injection) and (resonator or resonant) and (end near3 face)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:26
S19	4	372/75,96,97.ccls. and (semiconductor and substrate and active and cladding and (contact near3 layer) and (insulate or insulating) and (electrode) and (ridge) and (current near3 injection) and (resonator or resonant) and (end near3 face))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:27
S20	20	372/75,96,97.ccls. and (semiconductor and substrate and active and cladding and (contact near3 layer) and (insulate or insulating) and (electrode) and (ridge) and (current near3 injection))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:27
S21	20	372/75,96,97.ccls. and (semiconductor and substrate and (active near3 layer) and cladding and (contact near3 layer) and (insulate or insulating) and (electrode) and (ridge) and (current near3 injection))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:30
S22	114	372/43-50.ccls.and (semiconductor and substrate and (active near3 layer) and cladding and (contact near3 layer) and (insulate or insulating) and (electrode) and (ridge) and (current near3 injection))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:51
S23	18	372/43-50.ccls. and (semiconductor and substrate and active and cladding and (contact near3 layer) and (insulate or insulating) and (electrode) and (ridge) and (current near3 injection) and (resonator or resonant) and (end near3 face))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:29

S24	64	372/43-50.ccls.and (semiconductor and substrate and (active near3 layer) and cladding and (contact near3 layer) and (insulate or insulating) and (electrode) and (ridge) and (current near3 injection) and (AlGaAs and GaAs))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:31
S25	6	372/43-50.ccls.and (semiconductor and substrate and (active near3 layer) and cladding and (contact near3 layer) and (insulate or insulating) and (electrode) and (ridge) and (current near3 injection) and ((AlGaAs near3 cladding) and (GaAs near3 (contact or electrode))) and InGaP)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:32
S26	6	372/43-50.ccls. and (semiconductor and substrate and (active near3 layer) and cladding and (contact near3 layer) and (insulate or insulating) and (electrode) and (ridge) and (current near3 injection) and ((AlGaAs near3 cladding) and (GaAs near3 (contact or electrode))) and InGaP)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:33
S27	6	(semiconductor and substrate and (active near3 layer) and cladding and (contact near3 layer) and (insulate or insulating) and (electrode) and (ridge) and (current near3 injection) and ((AlGaAs near3 cladding) and (GaAs near3 (contact or electrode))) and InGaP)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:34
S28	22	372/43-50.ccls.and (semiconductor and substrate and (active near3 layer) and cladding and (contact near3 layer) and (insulate or insulating) and (electrode) and (ridge) and (current near3 injection) and ((AlGaAs near3 cladding) and (GaAs near3 (contact or electrode))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:36
S29	1810	372/43-50.ccls.and (cladding and (quantum near3 well))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:36

S30	1659	372/43-50.ccls.and (cladding and (quantum near3 well) and (active near3 layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:37
S31	952	372/43-50.ccls.and (cladding and (quantum near3 well) and (active near3 layer) and (barrier near3 layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:37
S32	505	372/43-50.ccls.and (((first and second) near3 cladding) and (quantum near3 well) and (active near3 layer) and (barrier near3 layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:37
S33	364	372/43-50.ccls.and (((first and second) near3 cladding) and (quantum near3 well) and (active near3 layer) and (barrier near3 layer) and (GaAs near3 substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:38
S34	85	372/43-50.ccls.and (((first and second) near3 cladding) and (quantum near3 well) and (active near3 layer) and (barrier near3 layer) and (GaAs near3 substrate) and (tensile near3 strain))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:38
S35	40	372/43-50.ccls.and (((first and second) near3 cladding) and (quantum near3 well) and (active near3 layer) and (barrier near3 layer) and (GaAs near3 substrate) and (tensile near3 strain) and (current near3 region))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:39
S36	5	372/43-50.ccls.and (((first and second) near3 cladding) and (quantum near3 well) and (active near3 layer) and (barrier near3 layer) and (GaAs near3 substrate) and (tensile near3 strain) and (current near3 region) and (non adj2 injection))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:40
S37	7	("6127691" | "6285695" | "6356572" | "6396863" | "6400743" | "6516016" | "6546033").PN.	USPAT	OR	OFF	2004/07/21 16:40
S38	5	372/43-50.ccls. and (((first and second) near3 cladding) and (quantum near3 well) and (active near3 layer) and (barrier near3 layer) and (GaAs near3 substrate) and (tensile near3 strain) and (current near3 region) and (non adj2 injection))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:51

S39	6	semiconductor and (((first and second) near3 cladding) and (quantum near3 well) and (active near3 layer) and (barrier near3 layer) and (GaAs near3 substrate) and (tensile near3 strain) and (current near3 region) and (non adj2 injection))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:51
S40	156021	fuji adj3 photo adj3 film	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/21 16:52
S41	4	(fuji adj3 photo adj3 film) and (((first and second) near3 cladding) and (quantum near3 well) and (active near3 layer) and (barrier near3 layer) and (GaAs near3 substrate) and (tensile near3 strain) and (current near3 region) and (non adj2 injection))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/07/22 09:07
S42	0	"20020146051".URPN.	USPAT	OR	OFF	2004/07/21 16:54
S43	7	("6127691" | "6285695" | "6356572" | "6396863" | "6400743" | "6516016" | "6546033").PN.	USPAT	OR	OFF	2004/07/21 16:54
S44	7	(("6127691") or ("6285695") or ("6356572") or ("6396863") or ("6400743") or ("6516016") or ("6546033")).PN.	USPAT; USOCR	OR	OFF	2004/07/21 16:56
S45	7	("6127691" | "6285695" | "6356572" | "6396863" | "6400743" | "6516016" | "6546033").PN.	USPAT	OR	OFF	2004/07/22 08:42
S46	1	("4371966").PN.	USPAT; USOCR	OR	OFF	2004/07/22 09:14
S47	4	("4270096" | "4282494" | "4297652" | "4321556").PN.	USPAT	OR	OFF	2004/07/22 09:08
S48	2	("3824493" | "4105955").PN.	USPAT	OR	OFF	2004/07/22 09:08
S49	16	"4282494".URPN.	USPAT	OR	OFF	2004/07/22 09:09
S50	3	"4270096".URPN.	USPAT	OR	OFF	2004/07/22 09:09
S51	16	"4371966".URPN.	USPAT	OR	OFF	2004/07/22 09:10
S52	2	JP-09298340-$.did.	EPO; JPO; DERWENT	OR	ON	2004/07/22 09:13
S53	2	JP-63038279-$.did.	EPO; JPO; DERWENT	OR	ON	2004/07/22 09:13
S54	2	JP-05327112-$.did.	EPO; JPO; DERWENT	OR	ON	2004/07/22 09:13

| S55 | 2 | (("4371966") or ("5394421")).PN. | USPAT; USOCR | OR | OFF | 2004/07/22 09:15 |